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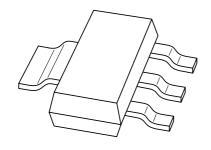
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



BSP126

N-channel enhancement mode vertical D-MOS transistor

Product specification Supersedes data of 1997 Jun 23 2002 Feb 19





N-channel enhancement mode vertical D-MOS transistor

BSP126

FEATURES

- Direct interface to C-MOS, TTL, etc.
- High-speed switching
- No secondary breakdown.

APPLICATIONS

- Line current interruptor in telephone sets
- Relay, high-speed and line transformer drivers.

DESCRIPTION

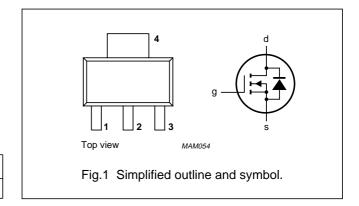
N-channel enhancement mode vertical D-MOS transistor in a miniature SOT223 package.

MARKING

TYPE NUMBER	MARKING CODE	
BSP126	BSP126	

PINNING - SOT223

PIN	DESCRIPTION
1	gate
2	drain
3	source
4	drain



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V _{DS}	drain-source voltage (DC)		_	250	V
I _D	drain current (DC)		_	375	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	_	1.5	W
R _{DSon}	drain-source on-state resistance	$I_D = 300 \text{ mA}; V_{GS} = 10 \text{ V}$	2.8	5	Ω
V_{GSth}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$	_	2	٧

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{DS}	drain-source voltage (DC)		_	250	V
V _{GSO}	gate-source voltage (DC)	open drain	_	±20	V
I _D	drain current (DC)		_	375	mA
I _{DM}	peak drain current		_	1.3	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	1.5	W
T _{stg}	storage temperature		-55	+150	°C
Tj	junction temperature		_	150	°C

Note

1. Device mounted on a $40 \times 40 \times 1.5$ mm epoxy printed-circuit board; mounting pad for the drain tab minimum 6 cm².

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient; note 1	83.3	K/W

Note

1. Device mounted on a $40 \times 40 \times 1.5$ mm epoxy printed-circuit board; mounting pad for the drain tab minimum 6 cm².

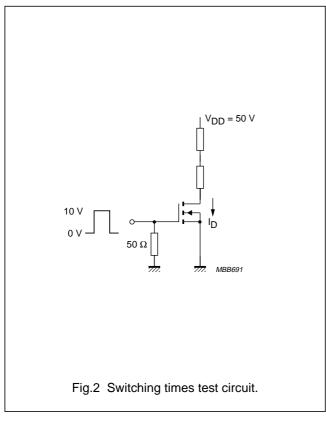
CHARACTERISTICS

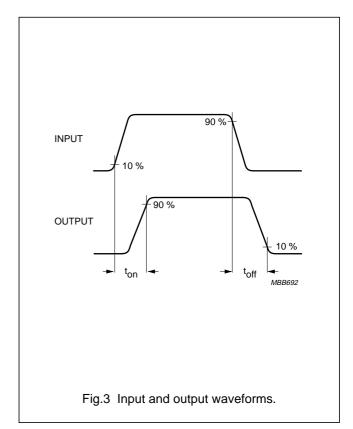
 $T_i = 25$ °C unless otherwise specified.

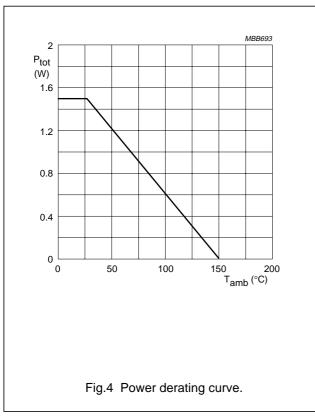
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 10 \mu\text{A}; V_{GS} = 0$	250	_	_	V
I _{GSS}	gate-source leakage current	V _{GS} = ±20 V; V _{DS} = 0	_	_	±100	nA
V _{GSth}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$	0.8	_	2	V
R _{DSon}	drain-source on-state resistance	$I_D = 20 \text{ mA}; V_{GS} = 2.4 \text{ V}$	-	_	7.5	Ω
		$I_D = 300 \text{ mA}; V_{GS} = 10 \text{ V}$	_	2.8	5	Ω
I _{DSS}	drain-source leakage current	V _{DS} = 200 V; V _{GS} = 0	_	_	1	μΑ
Y _{fs}	transfer admittance	$I_D = 300 \text{ mA}; V_{DS} = 25 \text{ V}$	200	600	_	mS
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0; f = 1 MHz	Ī-	100	120	pF
Coss	output capacitance	V _{DS} = 25 V; V _{GS} = 0; f = 1 MHz	Ī-	21	30	pF
C _{rss}	feedback capacitance	V _{DS} = 25 V; V _{GS} = 0; f = 1 MHz	-	10	15	pF
Switching tir	nes (see Figs 2 and 3)	•	•			
t _{on}	turn-on time	$I_D = 250 \text{ mA}; V_{DD} = 50 \text{ V};$ $V_{GS} = 0 \text{ to } 10 \text{ V}$	-	6	10	ns
t _{off}	turn-off time	$I_D = 250 \text{ mA}; V_{DD} = 50 \text{ V};$ $V_{GS} = 10 \text{ to } 0 \text{ V}$	-	47	60	ns

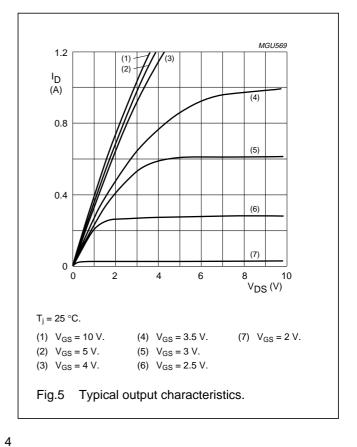
N-channel enhancement mode vertical D-MOS transistor

BSP126





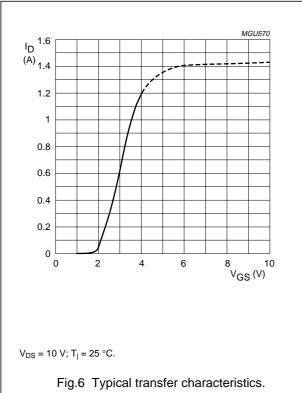


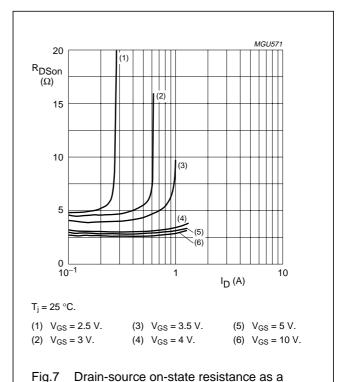


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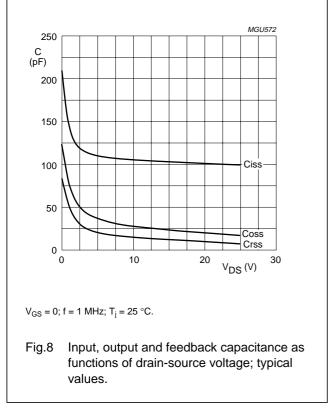
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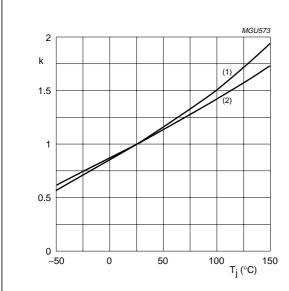


function of drain current; typical values.



N-channel enhancement mode vertical D-MOS transistor

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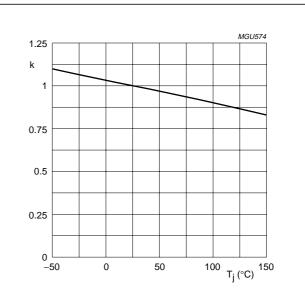
$$k = \frac{R_{DSon} at T_j}{R_{DSon} at 25 °C}$$

Typical R_{DSon:}

(1) $I_D = 250 \text{ mA}$; $V_{GS} = 10 \text{ V}$.

(2) $I_D = 20 \text{ mA}$; $V_{GS} = 2.4 \text{ V}$.

Fig.9 Temperature coefficient of drain-source on-state resistance; typical values.



$$k = \frac{V_{GSth} \text{ at } T_j}{V_{GSth} \text{ at 25 } ^{\circ}C}$$

Typical V_{GSth} at 1 mA.

Fig.10 Temperature coefficient of gate-source threshold voltage; typical values.

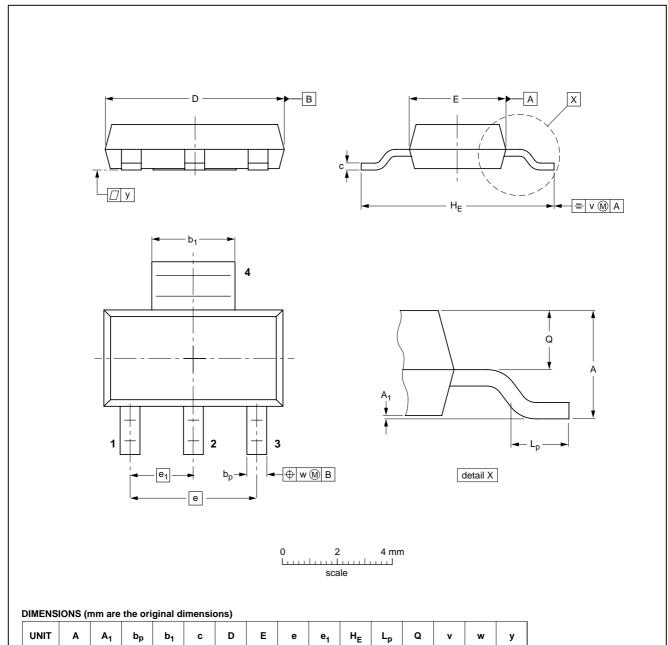
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PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



OUTLINE		REFERENCES		REFER		EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ		PROJECTION ISSUE DAT		
SOT223			SC-73			97-02-28 99-09-13	

2.3

0.95

0.1

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2.9

0.32

0.22

6.7

3.7

0.10

0.01

0.80

0.60

1.8

1.5

mm

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DATA SHEET STATUS

DATA SHEET STATUS(1)	PRODUCT STATUS ⁽²⁾	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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NOTES

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NOTES

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Contact information

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